Altera - EPF10K50ETC144-2 Datasheet

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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications,

Details	
Product Status	Active
Number of LABs/CLBs	360
Number of Logic Elements/Cells	2880
Total RAM Bits	40960
Number of I/O	102
Number of Gates	116000
Voltage - Supply	2.375V ~ 2.625V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 70°C (TA)
Package / Case	144-LQFP
Supplier Device Package	144-TQFP (20x20)
Purchase URL	https://www.e-xfl.com/pro/item?MUrl=&PartUrl=epf10k50etc144-2

Table 4. FLEX 10KE Package Sizes

Device	144-Pin TQFP	208-Pin PQFP	240-Pin PQFP RQFP	256-Pin FineLine BGA	356-Pin BGA	484-Pin FineLine BGA	599-Pin PGA	600-Pin BGA	672-Pin FineLine BGA
Pitch (mm)	0.50	0.50	0.50	1.0	1.27	1.0	–	1.27	1.0
Area (mm^2)	484	936	1,197	289	1,225	529	3,904	2,025	729
Length × width (mm × mm)	22 × 22	30.6 × 30.6	34.6 × 34.6	17 × 17	35 × 35	23 × 23	62.5 × 62.5	45 × 45	27 × 27

General Description

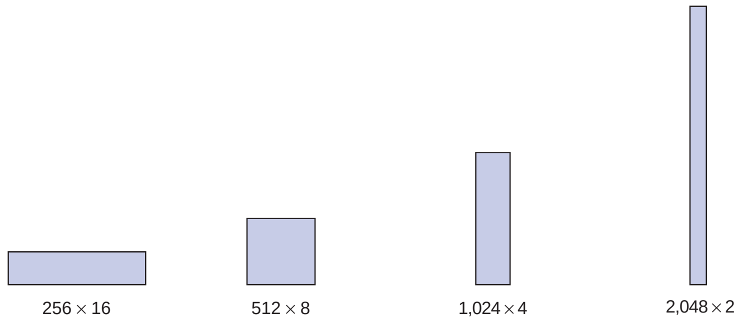
Altera FLEX 10KE devices are enhanced versions of FLEX 10K devices. Based on reconfigurable CMOS SRAM elements, the FLEX architecture incorporates all features necessary to implement common gate array megafunctions. With up to 200,000 typical gates, FLEX 10KE devices provide the density, speed, and features to integrate entire systems, including multiple 32-bit buses, into a single device.

The ability to reconfigure FLEX 10KE devices enables 100% testing prior to shipment and allows the designer to focus on simulation and design verification. FLEX 10KE reconfigurability eliminates inventory management for gate array designs and generation of test vectors for fault coverage.

Table 5 shows FLEX 10KE performance for some common designs. All performance values were obtained with Synopsys DesignWare or LPM functions. Special design techniques are not required to implement the applications; the designer simply infers or instantiates a function in a Verilog HDL, VHDL, Altera Hardware Description Language (AHDL), or schematic design file.

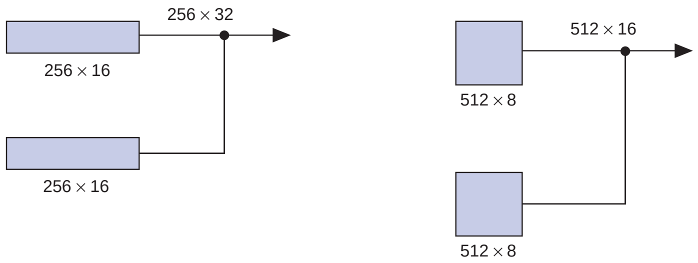
When used as RAM, each EAB can be configured in any of the following sizes: 256 × 16, 512 × 8, 1,024 × 4, or 2,048 × 2 (see Figure 5).

Figure 5. FLEX 10KE EAB Memory Configurations



Larger blocks of RAM are created by combining multiple EABs. For example, two 256 × 16 RAM blocks can be combined to form a 256 × 32 block; two 512 × 8 RAM blocks can be combined to form a 512 × 16 block (see Figure 6).

Figure 6. Examples of Combining FLEX 10KE EABs



If necessary, all EABs in a device can be cascaded to form a single RAM block. EABs can be cascaded to form RAM blocks of up to 2,048 words without impacting timing. The Altera software automatically combines EABs to meet a designer's RAM specifications.

EABs provide flexible options for driving and controlling clock signals. Different clocks and clock enables can be used for reading and writing to the EAB. Registers can be independently inserted on the data input, EAB output, write address, write enable signals, read address, and read enable signals. The global signals and the EAB local interconnect can drive write enable, read enable, and clock enable signals. The global signals, dedicated clock pins, and EAB local interconnect can drive the EAB clock signals. Because the LEs drive the EAB local interconnect, the LEs can control write enable, read enable, clear, clock, and clock enable signals.

An EAB is fed by a row interconnect and can drive out to row and column interconnects. Each EAB output can drive up to two row channels and up to two column channels; the unused row channel can be driven by other LEs. This feature increases the routing resources available for EAB outputs (see Figures 2 and 4). The column interconnect, which is adjacent to the EAB, has twice as many channels as other columns in the device.

Logic Array Block

An LAB consists of eight LEs, their associated carry and cascade chains, LAB control signals, and the LAB local interconnect. The LAB provides the coarse-grained structure to the FLEX 10KE architecture, facilitating efficient routing with optimum device utilization and high performance (see Figure 7).

Figure 11 shows the LE operating modes.

Figure 11. FLEX 10KE LE Operating Modes

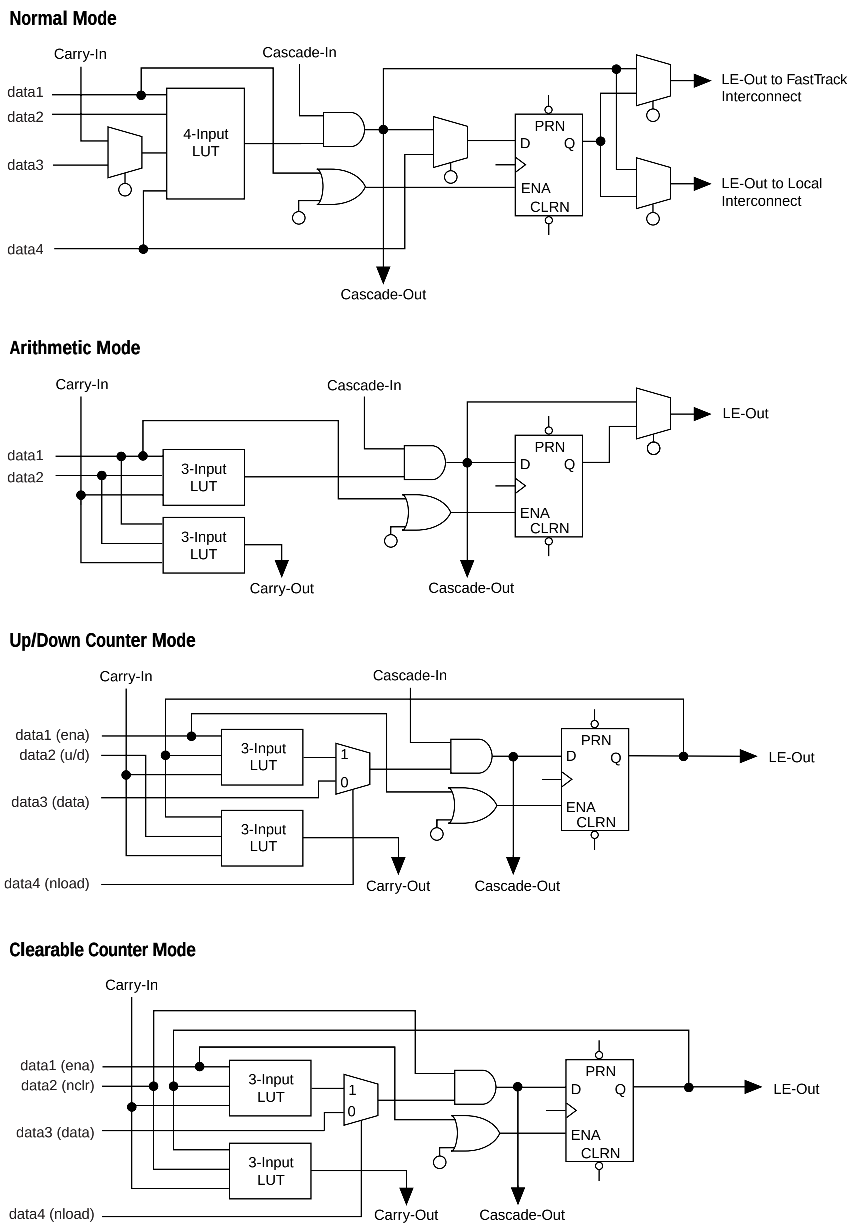
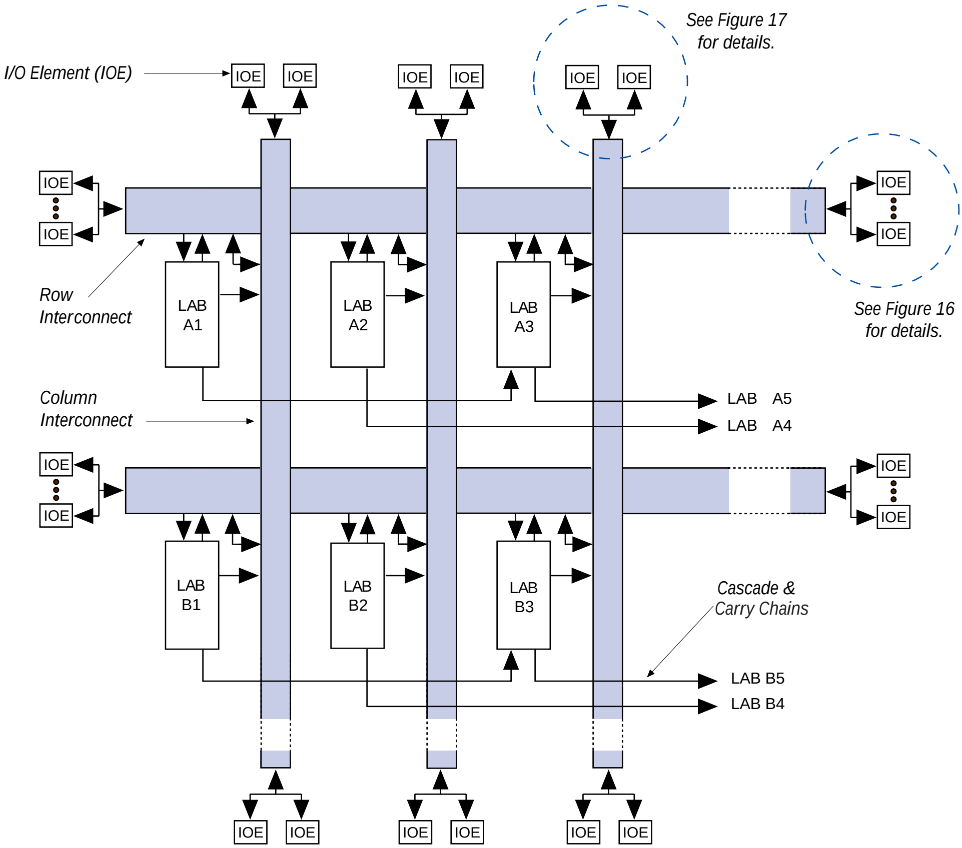


Figure 14. FLEX 10KE Interconnect Resources



I/O Element

An IOE contains a bidirectional I/O buffer and a register that can be used either as an input register for external data that requires a fast setup time, or as an output register for data that requires fast clock-to-output performance. In some cases, using an LE register for an input register will result in a faster setup time than using an IOE register. IOEs can be used as input, output, or bidirectional pins. For bidirectional registered I/O implementation, the output register should be in the IOE, and the data input and output enable registers should be LE registers placed adjacent to the bidirectional pin. The Altera Compiler uses the programmable inversion option to invert signals from the row and column interconnect automatically where appropriate. Figure 15 shows the bidirectional I/O registers.

On all FLEX 10KE devices (except EPF10K50E and EPF10K200E devices), the input path from the I/O pad to the FastTrack Interconnect has a programmable delay element that can be used to guarantee a zero hold time. EPF10K50S and EPF10K200S devices also support this feature. Depending on the placement of the IOE relative to what it is driving, the designer may choose to turn on the programmable delay to ensure a zero hold time or turn it off to minimize setup time. This feature is used to reduce setup time for complex pin-to-register paths (e.g., PCI designs).

Each IOE selects the clock, clear, clock enable, and output enable controls from a network of I/O control signals called the peripheral control bus. The peripheral control bus uses high-speed drivers to minimize signal skew across the device and provides up to 12 peripheral control signals that can be allocated as follows:

- Up to eight output enable signals
- Up to six clock enable signals
- Up to two clock signals
- Up to two clear signals

If more than six clock enable or eight output enable signals are required, each IOE on the device can be controlled by clock enable and output enable signals driven by specific LEs. In addition to the two clock signals available on the peripheral control bus, each IOE can use one of two dedicated clock pins. Each peripheral control signal can be driven by any of the dedicated input pins or the first LE of each LAB in a particular row. In addition, a LE in a different row can drive a column interconnect, which causes a row interconnect to drive the peripheral control signal. The chip-wide reset signal resets all IOE registers, overriding any other control signals.

When a dedicated clock pin drives IOE registers, it can be inverted for all IOEs in the device. All IOEs must use the same sense of the clock. For example, if any IOE uses the inverted clock, all IOEs must use the inverted clock and no IOE can use the non-inverted clock. However, LEs can still use the true or complement of the clock on a LAB-by-LAB basis.

The incoming signal may be inverted at the dedicated clock pin and will drive all IOEs. For the true and complement of a clock to be used to drive IOEs, drive it into both global clock pins. One global clock pin will supply the true, and the other will supply the complement.

When the true and complement of a dedicated input drives IOE clocks, two signals on the peripheral control bus are consumed, one for each sense of the clock.

Column-to-IOE Connections

When an IOE is used as an input, it can drive up to two separate column channels. When an IOE is used as an output, the signal is driven by a multiplexer that selects a signal from the column channels. Two IOEs connect to each side of the column channels. Each IOE can be driven by column channels via a multiplexer. The set of column channels is different for each IOE (see Figure 17).

Figure 17. FLEX 10KE Column-to-IOE Connections

The values for m and n are provided in Table 11.

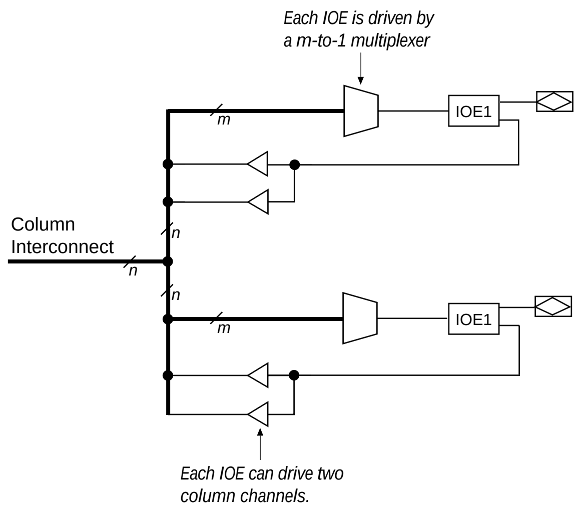


Table 11 lists the FLEX 10KE column-to-IOE interconnect resources.

Table 11. FLEX 10KE Column-to-IOE Interconnect Resources

Device	Channels per Column *(n)*	Column Channels per Pin *(m)*
EPF10K30E	24	16
EPF10K50E EPF10K50S	24	16
EPF10K100E	24	16
EPF10K130E	32	24
EPF10K200E EPF10K200S	48	40

IEEE Std. 1149.1 (JTAG) Boundary-Scan Support

All FLEX 10KE devices provide JTAG BST circuitry that complies with the IEEE Std. 1149.1-1990 specification. FLEX 10KE devices can also be configured using the JTAG pins through the BitBlaster or ByteBlasterMV download cable, or via hardware that uses the Jam™ STAPL programming and test language. JTAG boundary-scan testing can be performed before or after configuration, but not during configuration. FLEX 10KE devices support the JTAG instructions shown in Table 15.

Table 15. FLEX 10KE JTAG Instructions

JTAG Instruction	Description
SAMPLE/PRELOAD	Allows a snapshot of signals at the device pins to be captured and examined during normal device operation, and permits an initial data pattern to be output at the device pins.
EXTEST	Allows the external circuitry and board-level interconnections to be tested by forcing a test pattern at the output pins and capturing test results at the input pins.
BYPASS	Places the 1-bit bypass register between the `TDI` and `TDO` pins, which allows the BST data to pass synchronously through a selected device to adjacent devices during normal device operation.
USERCODE	Selects the user electronic signature (USERCODE) register and places it between the `TDI` and `TDO` pins, allowing the USERCODE to be serially shifted out of `TDO`.
IDCODE	Selects the IDCODE register and places it between `TDI` and `TDO`, allowing the IDCODE to be serially shifted out of `TDO`.
ICR Instructions	These instructions are used when configuring a FLEX 10KE device via JTAG ports with a BitBlaster or ByteBlasterMV download cable, or using a Jam File (**.jam**) or Jam Byte-Code File (**.jbc**) via an embedded processor.

The instruction register length of FLEX 10KE devices is 10 bits. The USERCODE register length in FLEX 10KE devices is 32 bits; 7 bits are determined by the user, and 25 bits are pre-determined. Tables 16 and 17 show the boundary-scan register length and device IDCODE information for FLEX 10KE devices.

Table 16. FLEX 10KE Boundary-Scan Register Length

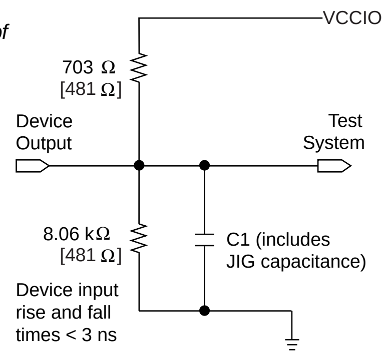
Device	Boundary-Scan Register Length
EPF10K30E	690
EPF10K50E EPF10K50S	798
EPF10K100E	1,050
EPF10K130E	1,308
EPF10K200E EPF10K200S	1,446

Generic Testing

Each FLEX 10KE device is functionally tested. Complete testing of each configurable static random access memory (SRAM) bit and all logic functionality ensures 100% yield. AC test measurements for FLEX 10KE devices are made under conditions equivalent to those shown in Figure 21. Multiple test patterns can be used to configure devices during all stages of the production flow.

Figure 21. FLEX 10KE AC Test Conditions

Power supply transients can affect AC measurements. Simultaneous transitions of multiple outputs should be avoided for accurate measurement. Threshold tests must not be performed under AC conditions. Large-amplitude, fast-ground-current transients normally occur as the device outputs discharge the load capacitances. When these transients flow through the parasitic inductance between the device ground pin and the test system ground, significant reductions in observable noise immunity can result. Numbers in brackets are for 2.5-V devices or outputs. Numbers without brackets are for 3.3-V. devices or outputs.



Operating Conditions

Tables 19 through 23 provide information on absolute maximum ratings, recommended operating conditions, DC operating conditions, and capacitance for 2.5-V FLEX 10KE devices.

Table 19. FLEX 10KE 2.5-V Device Absolute Maximum Ratings *Note (1)*

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CCINT}	Supply voltage	With respect to ground *(2)*	–0.5	3.6	V
V_{CCIO}			–0.5	4.6	V
V_I	DC input voltage		–2.0	5.75	V
I_{OUT}	DC output current, per pin		–25	25	mA
T_{STG}	Storage temperature	No bias	–65	150	° C
T_{AMB}	Ambient temperature	Under bias	–65	135	° C
T_J	Junction temperature	PQFP, TQFP, BGA, and FineLine BGA packages, under bias		135	° C
		Ceramic PGA packages, under bias		150	° C

Table 20. 2.5-V EPF10K50E & EPF10K200E Device Recommended Operating Conditions					
Symbol	**Parameter**	**Conditions**	**Min**	**Max**	**Unit**
V_{CCINT}	Supply voltage for internal logic and input buffers	*(3)*, *(4)*	2.30 (2.30)	2.70 (2.70)	V
V_{CCIO}	Supply voltage for output buffers, 3.3-V operation	*(3)*, *(4)*	3.00 (3.00)	3.60 (3.60)	V
	Supply voltage for output buffers, 2.5-V operation	*(3)*, *(4)*	2.30 (2.30)	2.70 (2.70)	V
V_I	Input voltage	*(5)*	–0.5	5.75	V
V_O	Output voltage		0	V_{CCIO}	V
T_A	Ambient temperature	For commercial use	0	70	° C
		For industrial use	–40	85	° C
T_J	Operating temperature	For commercial use	0	85	° C
		For industrial use	–40	100	° C
t_R	Input rise time			40	ns
t_F	Input fall time			40	ns

Table 21. 2.5-V EPF10K30E, EPF10K50S, EPF10K100E, EPF10K130E & EPF10K200S Device Recommended Operating Conditions					
Symbol	**Parameter**	**Conditions**	**Min**	**Max**	**Unit**
V_{CCINT}	Supply voltage for internal logic and input buffers	*(3)*, *(4)*	2.375 (2.375)	2.625 (2.625)	V
V_{CCIO}	Supply voltage for output buffers, 3.3-V operation	*(3)*, *(4)*	3.00 (3.00)	3.60 (3.60)	V
	Supply voltage for output buffers, 2.5-V operation	*(3)*, *(4)*	2.375 (2.375)	2.625 (2.625)	V
V_I	Input voltage	*(5)*	–0.5	5.75	V
V_O	Output voltage		0	V_{CCIO}	V
T_A	Ambient temperature	For commercial use	0	70	° C
		For industrial use	–40	85	° C
T_J	Operating temperature	For commercial use	0	85	° C
		For industrial use	–40	100	° C
t_R	Input rise time			40	ns
t_F	Input fall time			40	ns

Figure 22 shows the required relationship between V_{CCIO} and V_{CCINT} for 3.3-V PCI compliance.

Figure 22. Relationship between V_{CCIO} & V_{CCINT} for 3.3-V PCI Compliance

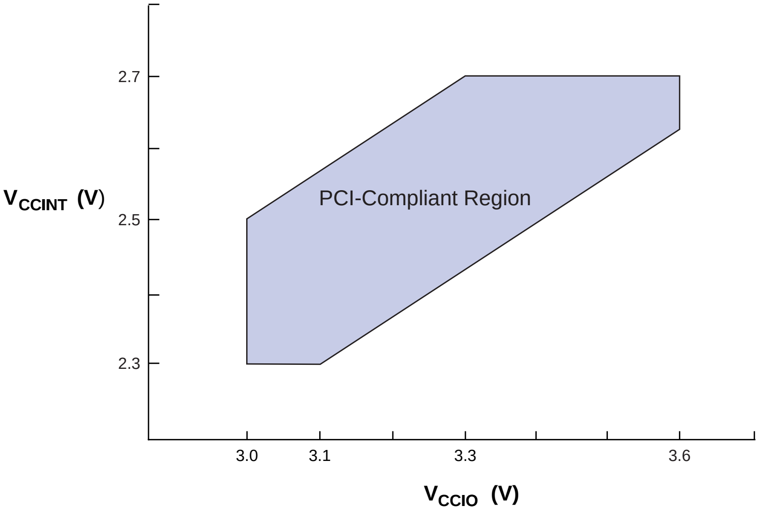


Figure 23 shows the typical output drive characteristics of FLEX 10KE devices with 3.3-V and 2.5-V V_{CCIO}. The output driver is compliant to the 3.3-V ***PCI Local Bus Specification, Revision 2.2*** (when `VCCIO` pins are connected to 3.3 V). FLEX 10KE devices with a -1 speed grade also comply with the drive strength requirements of the ***PCI Local Bus Specification, Revision 2.2*** (when `VCCINT` pins are powered with a minimum supply of 2.375 V, and `VCCIO` pins are connected to 3.3 V). Therefore, these devices can be used in open 5.0-V PCI systems.

Table 24. LE Timing Microparameters (Part 2 of 2) *Note (1)*		
Symbol	**Parameter**	**Condition**
t_{CLR}	LE register clear delay	
t_{CH}	Minimum clock high time from clock pin	
t_{CL}	Minimum clock low time from clock pin	

Table 25. IOE Timing Microparameters *Note (1)*		
Symbol	**Parameter**	**Conditions**
t_{IOD}	IOE data delay	
t_{IOC}	IOE register control signal delay	
t_{IOCO}	IOE register clock-to-output delay	
t_{IOCOMB}	IOE combinatorial delay	
t_{IOSU}	IOE register setup time for data and enable signals before clock; IOE register recovery time after asynchronous clear	
t_{IOH}	IOE register hold time for data and enable signals after clock	
t_{IOCLR}	IOE register clear time	
t_{OD1}	Output buffer and pad delay, slow slew rate = off, V_{CCIO} = 3.3 V	C1 = 35 pF *(2)*
t_{OD2}	Output buffer and pad delay, slow slew rate = off, V_{CCIO} = 2.5 V	C1 = 35 pF *(3)*
t_{OD3}	Output buffer and pad delay, slow slew rate = on	C1 = 35 pF *(4)*
t_{XZ}	IOE output buffer disable delay	
t_{ZX1}	IOE output buffer enable delay, slow slew rate = off, V_{CCIO} = 3.3 V	C1 = 35 pF *(2)*
t_{ZX2}	IOE output buffer enable delay, slow slew rate = off, V_{CCIO} = 2.5 V	C1 = 35 pF *(3)*
t_{ZX3}	IOE output buffer enable delay, slow slew rate = on	C1 = 35 pF *(4)*
t_{INREG}	IOE input pad and buffer to IOE register delay	
t_{IOFD}	IOE register feedback delay	
t_{INCOMB}	IOE input pad and buffer to FastTrack Interconnect delay	

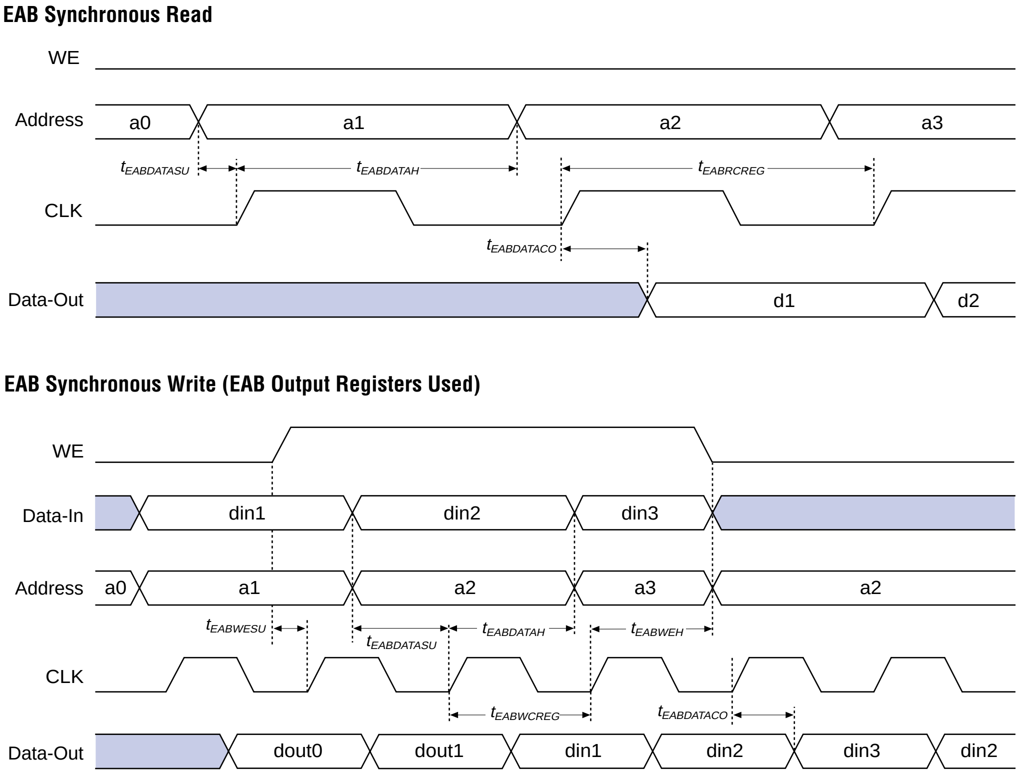
Table 30. External Bidirectional Timing Parameters *Note (9)*

Symbol	Parameter	Conditions
$t_{INSUBIDIR}$	Setup time for bi-directional pins with global clock at same-row or same-column LE register	
$t_{INHBIDIR}$	Hold time for bidirectional pins with global clock at same-row or same-column LE register	
t_{INH}	Hold time with global clock at IOE register	
$t_{OUTCOBIDIR}$	Clock-to-output delay for bidirectional pins with global clock at IOE register	C1 = 35 pF
$t_{XZBIDIR}$	Synchronous IOE output buffer disable delay	C1 = 35 pF
$t_{ZXBIDIR}$	Synchronous IOE output buffer enable delay, slow slew rate= off	C1 = 35 pF

Notes to tables:

(1) Microparameters are timing delays contributed by individual architectural elements. These parameters cannot be measured explicitly.
(2) Operating conditions: VCCIO = 3.3 V ±10% for commercial or industrial use.
(3) Operating conditions: VCCIO = 2.5 V ±5% for commercial or industrial use in EPF10K30E, EPF10K50S, EPF10K100E, EPF10K130E, and EPF10K200S devices.
(4) Operating conditions: VCCIO = 3.3 V.
(5) Because the RAM in the EAB is self-timed, this parameter can be ignored when the WE signal is registered.
(6) EAB macroparameters are internal parameters that can simplify predicting the behavior of an EAB at its boundary; these parameters are calculated by summing selected microparameters.
(7) These parameters are worst-case values for typical applications. Post-compilation timing simulation and timing analysis are required to determine actual worst-case performance.
(8) Contact Altera Applications for test circuit specifications and test conditions.
(9) This timing parameter is sample-tested only.
(10) This parameter is measured with the measurement and test conditions, including load, specified in the PCI Local Bus Specification, revision 2.2.

Figure 30. EAB Synchronous Timing Waveforms



Tables 31 through 37 show EPF10K30E device internal and external timing parameters.

Table 31. EPF10K30E Device LE Timing Microparameters (Part 1 of 2) Note (1)

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{LUT}		0.7		0.8		1.1	ns
t_{CLUT}		0.5		0.6		0.8	ns
t_{RLUT}		0.6		0.7		1.0	ns
t_{PACKED}		0.3		0.4		0.5	ns
t_{EN}		0.6		0.8		1.0	ns
t_{CICO}		0.1		0.1		0.2	ns
t_{CGEN}		0.4		0.5		0.7	ns

Table 33. EPF10K30E Device EAB Internal Microparameters *Note (1)*							
Symbol	**-1 Speed Grade**		**-2 Speed Grade**		**-3 Speed Grade**		**Unit**
	Min	**Max**	**Min**	**Max**	**Min**	**Max**	
$t_{EABDATA1}$		1.7		2.0		2.3	ns
$t_{EABDATA1}$		0.6		0.7		0.8	ns
t_{EABWE1}		1.1		1.3		1.4	ns
t_{EABWE2}		0.4		0.4		0.5	ns
t_{EABRE1}		0.8		0.9		1.0	ns
t_{EABRE2}		0.4		0.4		0.5	ns
t_{EABCLK}		0.0		0.0		0.0	ns
t_{EABCO}		0.3		0.3		0.4	ns
$t_{EABBYPASS}$		0.5		0.6		0.7	ns
t_{EABSU}	0.9		1.0		1.2		ns
t_{EABH}	0.4		0.4		0.5		ns
t_{EABCLR}	0.3		0.3		0.3		ns
t_{AA}		3.2		3.8		4.4	ns
t_{WP}	2.5		2.9		3.3		ns
t_{RP}	0.9		1.1		1.2		ns
t_{WDSU}	0.9		1.0		1.1		ns
t_{WDH}	0.1		0.1		0.1		ns
t_{WASU}	1.7		2.0		2.3		ns
t_{WAH}	1.8		2.1		2.4		ns
t_{RASU}	3.1		3.7		4.2		ns
t_{RAH}	0.2		0.2		0.2		ns
t_{WO}		2.5		2.9		3.3	ns
t_{DD}		2.5		2.9		3.3	ns
t_{EABOUT}		0.5		0.6		0.7	ns
t_{EABCH}	1.5		2.0		2.3		ns
t_{EABCL}	2.5		2.9		3.3		ns

Table 34. EPF10K30E Device EAB Internal Timing Macroparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{EABAA}		6.4		7.6		8.8	ns
$t_{EABRCOMB}$	6.4		7.6		8.8		ns
$t_{EABRCREG}$	4.4		5.1		6.0		ns
t_{EABWP}	2.5		2.9		3.3		ns
$t_{EABWCOMB}$	6.0		7.0		8.0		ns
$t_{EABWCREG}$	6.8		7.8		9.0		ns
t_{EABDD}		5.7		6.7		7.7	ns
$t_{EABDATACO}$		0.8		0.9		1.1	ns
$t_{EABDATASU}$	1.5		1.7		2.0		ns
$t_{EABDATAH}$	0.0		0.0		0.0		ns
$t_{EABWESU}$	1.3		1.4		1.7		ns
t_{EABWEH}	0.0		0.0		0.0		ns
$t_{EABWDSU}$	1.5		1.7		2.0		ns
t_{EABWDH}	0.0		0.0		0.0		ns
$t_{EABWASU}$	3.0		3.6		4.3		ns
t_{EABWAH}	0.5		0.5		0.4		ns
t_{EABWO}		5.1		6.0		6.8	ns

Table 37. EPF10K30E External Bidirectional Timing Parameters *Notes (1), (2)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{INSUBIDIR}$ *(3)*	2.8		3.9		5.2		ns
$t_{INHBIDIR}$ *(3)*	0.0		0.0		0.0		ns
$t_{INSUBIDIR}$ *(4)*	3.8		4.9		–		ns
$t_{INHBIDIR}$ *(4)*	0.0		0.0		–		ns
$t_{OUTCOBIDIR}$ *(3)*	2.0	4.9	2.0	5.9	2.0	7.6	ns
$t_{XZBIDIR}$ *(3)*		6.1		7.5		9.7	ns
$t_{ZXBIDIR}$ *(3)*		6.1		7.5		9.7	ns
$t_{OUTCOBIDIR}$ *(4)*	0.5	3.9	0.5	4.9	–	–	ns
$t_{XZBIDIR}$ *(4)*		5.1		6.5		–	ns
$t_{ZXBIDIR}$ *(4)*		5.1		6.5		–	ns

Notes to tables:

(1) All timing parameters are described in Tables 24 through 30 in this data sheet.
(2) These parameters are specified by characterization.
(3) This parameter is measured without the use of the ClockLock or ClockBoost circuits.
(4) This parameter is measured with the use of the ClockLock or ClockBoost circuits.

Tables 38 through 44 show EPF10K50E device internal and external timing parameters.

Table 38. EPF10K50E Device LE Timing Microparameters (Part 1 of 2) *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{LUT}		0.6		0.9		1.3	ns
t_{CLUT}		0.5		0.6		0.8	ns
t_{RLUT}		0.7		0.8		1.1	ns
t_{PACKED}		0.4		0.5		0.6	ns
t_{EN}		0.6		0.7		0.9	ns
t_{CICO}		0.2		0.2		0.3	ns
t_{CGEN}		0.5		0.5		0.8	ns
t_{CGENR}		0.2		0.2		0.3	ns
t_{CASC}		0.8		1.0		1.4	ns
t_{C}		0.5		0.6		0.8	ns
t_{CO}		0.7		0.7		0.9	ns
t_{COMB}		0.5		0.6		0.8	ns
t_{SU}	0.7		0.7		0.8		ns

Table 50. EPF10K100E External Timing Parameters *Notes (1), (2)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{DRR}		9.0		12.0		16.0	ns
t_{INSU} *(3)*	2.0		2.5		3.3		ns
t_{INH} *(3)*	0.0		0.0		0.0		ns
t_{OUTCO} *(3)*	2.0	5.2	2.0	6.9	2.0	9.1	ns
t_{INSU} *(4)*	2.0		2.2		–		ns
t_{INH} *(4)*	0.0		0.0		–		ns
t_{OUTCO} *(4)*	0.5	3.0	0.5	4.6	–	–	ns
t_{PCISU}	3.0		6.2		–		ns
t_{PCIH}	0.0		0.0		–		ns
t_{PCICO}	2.0	6.0	2.0	6.9	–	–	ns

Table 51. EPF10K100E External Bidirectional Timing Parameters *Notes (1), (2)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{INSUBIDIR}$ *(3)*	1.7		2.5		3.3		ns
$t_{INHBIDIR}$ *(3)*	0.0		0.0		0.0		ns
$t_{INSUBIDIR}$ *(4)*	2.0		2.8		–		ns
$t_{INHBIDIR}$ *(4)*	0.0		0.0		–		ns
$t_{OUTCOBIDIR}$ *(3)*	2.0	5.2	2.0	6.9	2.0	9.1	ns
$t_{XZBIDIR}$ *(3)*		5.6		7.5		10.1	ns
$t_{ZXBIDIR}$ *(3)*		5.6		7.5		10.1	ns
$t_{OUTCOBIDIR}$ *(4)*	0.5	3.0	0.5	4.6	–	–	ns
$t_{XZBIDIR}$ *(4)*		4.6		6.5		–	ns
$t_{ZXBIDIR}$ *(4)*		4.6		6.5		–	ns

Notes to tables:

(1) All timing parameters are described in Tables 24 through 30 in this data sheet.
(2) These parameters are specified by characterization.
(3) This parameter is measured without the use of the ClockLock or ClockBoost circuits.
(4) This parameter is measured with the use of the ClockLock or ClockBoost circuits.

Table 56. EPF10K130E Device Interconnect Timing Microparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{DIN2IOE}$		2.8		3.5		4.4	ns
t_{DIN2LE}		0.7		1.2		1.6	ns
$t_{DIN2DATA}$		1.6		1.9		2.2	ns
$t_{DCLK2IOE}$		1.6		2.1		2.7	ns
$t_{DCLK2LE}$		0.7		1.2		1.6	ns
$t_{SAMELAB}$		0.1		0.2		0.2	ns
$t_{SAMEROW}$		1.9		3.4		5.1	ns
$t_{SAMECOLUMN}$		0.9		2.6		4.4	ns
$t_{DIFFROW}$		2.8		6.0		9.5	ns
$t_{TWOROWS}$		4.7		9.4		14.6	ns
$t_{LEPERIPH}$		3.1		4.7		6.9	ns
$t_{LABCARRY}$		0.6		0.8		1.0	ns
$t_{LABCASC}$		0.9		1.2		1.6	ns

Table 57. EPF10K130E External Timing Parameters *Notes (1), (2)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{DRR}		9.0		12.0		16.0	ns
t_{INSU} *(3)*	1.9		2.1		3.0		ns
t_{INH} *(3)*	0.0		0.0		0.0		ns
t_{OUTCO} *(3)*	2.0	5.0	2.0	7.0	2.0	9.2	ns
t_{INSU} *(4)*	0.9		1.1		–		ns
t_{INH} *(4)*	0.0		0.0		–		ns
t_{OUTCO} *(4)*	0.5	4.0	0.5	6.0	–	–	ns
t_{PCISU}	3.0		6.2		–		ns
t_{PCIH}	0.0		0.0		–		ns
t_{PCICO}	2.0	6.0	2.0	6.9	–	–	ns

Table 58. EPF10K130E External Bidirectional Timing Parameters *Notes (1), (2)*							
Symbol	**-1 Speed Grade**		**-2 Speed Grade**		**-3 Speed Grade**		**Unit**
	Min	**Max**	**Min**	**Max**	**Min**	**Max**	
$t_{INSUBIDIR}$ *(3)*	2.2		2.4		3.2		ns
$t_{INHBIDIR}$ *(3)*	0.0		0.0		0.0		ns
$t_{INSUBIDIR}$ *(4)*	2.8		3.0		–		ns
$t_{INHBIDIR}$ *(4)*	0.0		0.0		–		ns
$t_{OUTCOBIDIR}$ *(3)*	2.0	5.0	2.0	7.0	2.0	9.2	ns
$t_{XZBIDIR}$ *(3)*		5.6		8.1		10.8	ns
$t_{ZXBIDIR}$ *(3)*		5.6		8.1		10.8	ns
$t_{OUTCOBIDIR}$ *(4)*	0.5	4.0	0.5	6.0	–	–	ns
$t_{XZBIDIR}$ *(4)*		4.6		7.1		–	ns
$t_{ZXBIDIR}$ *(4)*		4.6		7.1		–	ns

Notes to tables:

(1) All timing parameters are described in Tables 24 through 30 in this data sheet.
(2) These parameters are specified by characterization.
(3) This parameter is measured without the use of the ClockLock or ClockBoost circuits.
(4) This parameter is measured with the use of the ClockLock or ClockBoost circuits.

Tables 59 through 65 show EPF10K200E device internal and external timing parameters.

Table 59. EPF10K200E Device LE Timing Microparameters *(Part 1 of 2)* *Note (1)*							
Symbol	**-1 Speed Grade**		**-2 Speed Grade**		**-3 Speed Grade**		**Unit**
	Min	**Max**	**Min**	**Max**	**Min**	**Max**	
t_{LUT}		0.7		0.8		1.2	ns
t_{CLUT}		0.4		0.5		0.6	ns
t_{RLUT}		0.6		0.7		0.9	ns
t_{PACKED}		0.3		0.5		0.7	ns
t_{EN}		0.4		0.5		0.6	ns
t_{CICO}		0.2		0.2		0.3	ns
t_{CGEN}		0.4		0.4		0.6	ns
t_{CGENR}		0.2		0.2		0.3	ns
t_{CASC}		0.7		0.8		1.2	ns
t_C		0.5		0.6		0.8	ns
t_{CO}		0.5		0.6		0.8	ns
t_{COMB}		0.4		0.6		0.8	ns
t_{SU}	0.4		0.6		0.7		ns